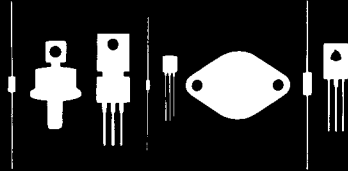


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145 Adams Avenue
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MJE370 PNP
MJE520 NPN

SILICON COMPLEMENTARY
POWER TRANSISTORS

JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE370, MJE520 types are Complementary Silicon Power Transistors designed for use in general purpose amplifier and switching applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNIT</u>
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	3.0	A
Collector Current (PEAK)	I_{CM}	7.0	A
Power Dissipation	PD	25	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +150	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	5.0	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNIT</u>
I_{CBO}	$V_{CB}=30\text{V}$		100	μA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	μA
BV_{CEO}	$I_C=100\text{mA}$	30		V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$	25		

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